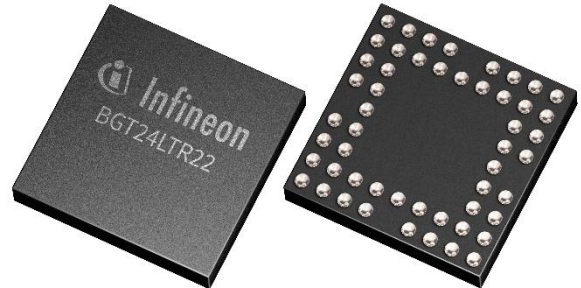


# BGT24LTR22

## Low Power Multichannel 24GHz Radar MMIC for Smart Sensing Applications

### Features

- 24 GHz transceiver MMIC (2 TX, 2 RX)
- Fully integrated low phase noise VCO
- Medium power amplifier with variable output power
- Integrated power detectors
- Homodyne low noise quadrature receivers
- Configurable analog baseband amplification stages
- Frequency divider
- Low power consumption
- Multimode operation (Master/Slave)
- Fully ESD protected device
- Single ended RF terminals
- Single supply voltage 1.5V
- WFWLB-52-3 pin plastic package sized 3.63mmx3.63mm
- Pb-free (RoHS compliant) package



### Potential Applications

- Smart home appliances
- Drone collision avoidance
- Traffic monitoring
- Security applications

### Description

BGT24LTR22 is a low power, low noise multi-channel Silicon Germanium transceiver MMIC for 24 GHz radar applications. It provides building blocks for analog signal generation and reception, operating in the frequency range from 24.0 GHz up to 24.25 GHz. Integrated digital blocks controlling the chip are implemented in order to support radar system design.

The device is manufactured in Infineon's B11HFC BiCMOS technology offering a cutoff frequency higher than 300GHz. It is housed in Infineon's plastic embedded Wafer Level Ball Grid Array (eWLB) package which can be processed in standard SMT flow.



**Table of Content**

- Features ..... 1**
- Potential Applications..... 1**
- Description ..... 1**
- Table of Content ..... 2**
- 1 Electrical Characteristics ..... 3**
  - 1.1 Absolute Maximum Ratings ..... 3
  - 1.2 ESD Integrity ..... 4
  - 1.3 Power Supply..... 4
  - 1.4 TX Section ..... 4
  - 1.5 RX Section ..... 5
  - 1.6 Frequency Divider ..... 6
- 2 SPI Interface..... 7**
  - 2.1 SPI Timing Requirements..... 7
- 3 Block Diagram and Pin Description..... 8**
  - 3.1 Block Diagram ..... 8
  - 3.2 Pin Out ..... 9
  - 3.3 Pin Definition and Function ..... 9
- 4 Package Dimensions and Footprint ..... 11**

## Electrical Characteristics

## 1 Electrical Characteristics

**Attention:** Test ■ means that the parameter is not subject to production test. It was verified by design or characterization respectively.

### 1.1 Absolute Maximum Ratings

**Table 1 Absolute Maximum Ratings:**  $T_A = -40\text{ °C} \dots 85\text{ °C}$ ; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Value			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Supply voltage	$V_{DD}$	-0.3	-	$V_{DD,max} + 0.3$	V	
DC voltage at RF pins	$V_{DC,RF}$	0	-	0	V	DC-short at RF pins (RX1, RX2, TX1, TX2) to GND
DC voltage at VCO tuning pin VTUNE	$V_{TUNE}$	0	-	5	V	
Voltage applied to all other user I/O pins	$V_{DC,I/O}$	-0.3	-	$V_{DD} + 0.3$	V	
RF input power RX inputs	$P_{RF}$	-	-	0	dBm	Pins RX1, RX2
Total power dissipation	$P_{DISS}$	-	-	500	mW	
Storage temperature range	$T_{STG}$	-40	-	150	°C	
Operational temperature range	$T_C$	-40	-	+85	°C	Temperature at package soldering point
Thermal resistance of package	$R_{th,P}$	-	18	-	K/W	Represents bulk silicon to package solder balls

**Attention:** Stresses exceeding the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

## Electrical Characteristics

## 1.2 ESD Integrity

Table 2 ESD integrity

Parameter	Symbol	Value			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
ESD robustness HBM <sup>1</sup>	$V_{ESD-HBM}$	-1	-	1	kV	All pins
ESD robustness CDM <sup>2</sup>	$V_{ESD-CDM}$	-500	-	500	V	All pins

1) According to ANSI/ESDA/JEDEC JS-001 (R = 1.5kOhm, C = 100pF) for Electrostatic Discharge Sensitivity Testing, Human Body Model (HBM)-Component Level

2) According to ESDA/JEDEC JS-002 Field-Induced Charged Device Model (CDM), Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components

Please note that this result is subject to:

- lot variations within the manufacturing process as specified by Infineon
- changes in the specific test setup

## 1.3 Power Supply

Table 3 Power Supply Electrical Characteristics:  $T_A = -40\text{ °C} \dots 85\text{ °C}$ 

Parameter	Symbol	Value			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Supply voltage	$V_{DD}$	1.45	1.5	1.6	V	
Supply current nominal operation mode	$I_{DD\_ON}$	-	170	230	mA	SPI Settings – Refer to AN607
Supply current in reduced power consumption mode	$I_{DD\_RED}$	-	135	-	mA	SPI Settings – Refer to AN607
Supply current standby-mode	$I_{DD\_STDBY}$	-	-	1	mA	SPI Settings – Refer to AN607

## 1.4 TX Section

Table 4 TX Section Electrical Characteristics:  $T_A = -40\text{ °C} \dots 85\text{ °C}$ ,  $V_{DD} = 1.45\text{ V} \dots 1.6\text{ V}$ ; all parameters are for master mode operation (unless otherwise specified)

Parameter	Symbol	Value			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
VCO frequency range	$f_{VCO}$	24.0	-	24.25	GHz	
VCO phase noise	$P_N$	-	-65 -85	-50 -70	dBc/Hz	@10kHz offset @100kHz offset
VCO AM noise	$P_{AM}$	-	-148	-	dBc/Hz	@100kHz offset
Tuning voltage to cover VCO frequency range	$V_{TUNE}$	0	0.7	3	V	ISM band covered from 0 V to 1.5 V

## Electrical Characteristics

**Table 4 TX Section Electrical Characteristics:**  $T_A = -40\text{ }^\circ\text{C} \dots 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.45\text{ V} \dots 1.6\text{ V}$ ; all parameters are for master mode operation (unless otherwise specified)

Parameter	Symbol	Value			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
VCO tuning sensitivity within VCO frequency range	$\Delta f / \Delta V_{TUNE}$	500	1600	3000	MHz/V	
VCO temperature drift within VCO frequency range	$\Delta f / \Delta T$	-	-5	-	MHz/K	
2 <sup>nd</sup> Harmonic suppression	$\Delta P_{fund,H2}$	15	27	-	dBc	
VCO nonharmonic suppression	$P_{SPUR}$	-	-55	-40	dBm	
TX output power <sup>1</sup>	$P_{TX1}$	1	5	9.5	dBm	
TX output power dynamic range	$\Delta P_{OUT}$	17	24	-	dB	
TX load impedance	$Z_{TX1}$	-	50	-	$\Omega$	Single-ended at outer edge of compensation structure on PCB as indicated in AN607

## 1.5 RX Section

**Table 5 RX Section Electrical Characteristics:**  $T_A = -40\text{ }^\circ\text{C} \dots 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.45\text{ V} \dots 1.6\text{ V}$ ; all parameters are within master mode operation (unless otherwise specified)

Parameter	Symbol	Value			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
RX frequency range	$f_{RX}$	24.0	-	24.25	GHz	
Single-sideband noise figure <sup>1</sup>	$NF_{SSB}$	-	8	16.5	dB	@ $f_{IF} = 200\text{ kHz}$ – Bypass Mode SPI configurable – Refer to AN607
		-	8.5	15.5		@ $f_{IF} = 200\text{ kHz}$ – ABB Mode SPI configurable – Refer to AN607
RF downconverter conversion gain <sup>1</sup>	$G_{DC}$	16	25	33	dB	@ $f_{IF} = 200\text{ kHz}$ – Bypass Mode SPI configurable – Refer to AN607
Analog baseband Gain	$G_{ABB}$	-	0/30/35/40/ 45/50/55/60	-	dB	Configurable via SPI
Input 1 dB compression point	$IP_{1dB}$	-	-19	-	dBm	RX in Bypass Mode
LO input power	$P_{LOIN}$	-	-10	-	dBm	For slave mode operation

<sup>1</sup> Refer to AN607 for more details about parameter variation over temperature

## Electrical Characteristics

**Table 5 RX Section Electrical Characteristics:**  $T_A = -40\text{ °C} \dots 85\text{ °C}$ ,  $V_{DD} = 1.45\text{ V} \dots 1.6\text{ V}$ ; all parameters are within master mode operation (unless otherwise specified)

Parameter	Symbol	Value			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Baseband high pass filters cut off frequency	$F_{c-hpf}$	-	20/50/80/100	-	kHz	Configurable via SPI 1 <sup>st</sup> order, -3 dB definition
Baseband low pass filters cut off frequency	$F_{c-lpf}$	-	600	-	kHz	4 <sup>th</sup> order, -3 dB definition
Quadrature phase imbalance	$\varepsilon_P$	-10	-	10	deg	
Quadrature amplitude imbalance	$\varepsilon_A$	-1.5	-	1.5	dB	
IF output impedance	$Z_{IF}$	-	400	-	$\Omega$	Differential
IF output impedance – Bypass Mode	$Z_{IFBY}$	-	1	-	k $\Omega$	Differential
IF output common mode voltage	$V_{IFCMD}$	-	0.75	-	V	
IF output power supply rejection ratio	$PSRR$	-	60	-	dB	@ DC
RX input impedance	$Z_{RXIN}$	-	50	-	$\Omega$	Single-ended at outer edge of compensation structure on PCB as indicated in AN607

## 1.6 Frequency Divider

**Table 6 Frequency Divider Electrical Characteristics:**  $T_A = -40\text{ °C} \dots 85\text{ °C}$ ,  $V_{DD} = 1.45\text{ V} \dots 1.6\text{ V}$ ,  
Freq = 24GHz

Parameter	Symbol	Value			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Dividing factor 1	$D_{DIV1}$	-	2 <sup>20</sup>	-	-	selectable via SPI
Dividing factor 2	$D_{DIV2}$	-	2 <sup>16</sup>	-	-	selectable via SPI
Dividing factor 3	$D_{DIV3}$	-	2 <sup>14</sup>	-	-	selectable via SPI
Dividing factor 4	$D_{DIV4}$	-	2 <sup>13</sup>	-	-	selectable via SPI
Dividing factor 5	$D_{DIV5}$	-	16	-	-	selectable via SPI
Divider output power	$P_{DIV5}$	-13	-5	0	dBm	For dividing factor 5 - @50 Ohms load
Divider output voltage range	$V_{DIV}$	0	-	$V_{DD}$	V	For dividing factors 1 to 4
External capacitive load	$C_{extLoad}$	-	-	15	pF	For dividing factors 1 to 4

SPI Interface

## 2 SPI Interface

### 2.1 SPI Timing Requirements

The BGT24LTR22 is configured using a 4-wire SPI interface. It is used to configure the internal modules of the BGT24LTR22 chip via registers. The main tasks are to set the mode of operation of the TX and/or RX chain and the baseband section. Communication with an external micro controller is done via the four dedicated pins SPIDI, SPIDO, SPICS and SPICLK. Figure 1 demonstrates how the timing of the SPI behaves. The “working edge” is the rising edge of the clock *SPICLK*. The master application processor presents data for BGT24LTR22 at the falling edge on *SPIDI*, BGT24LTR22 samples data at the rising edge. Read data is presented for the master on the rising edge on *SPIDO*. Refer to the application note AN607 for all details related to the SPI registers to control the MMIC.

*Note: Asynchronous reset (SPIRST) must be de-asserted at least 10 ns before the falling edge of SPICLK.*

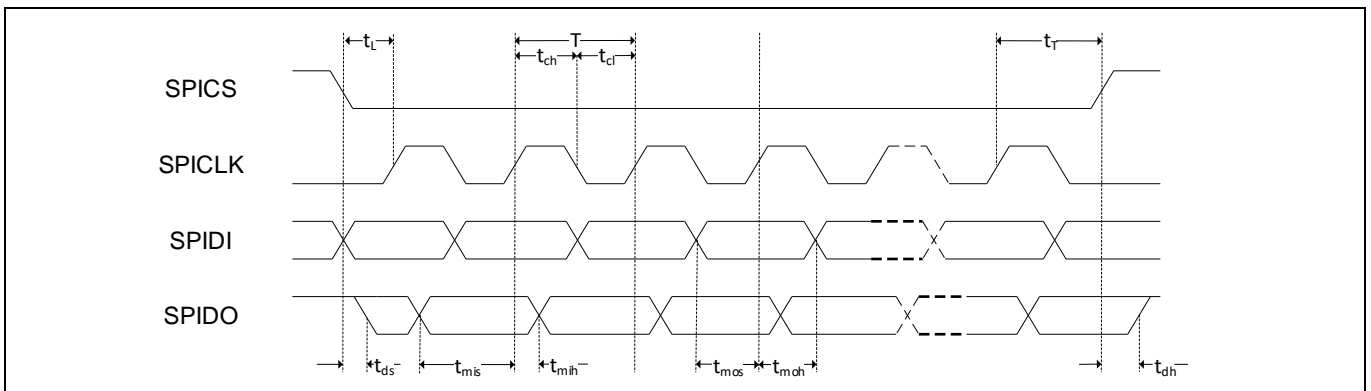


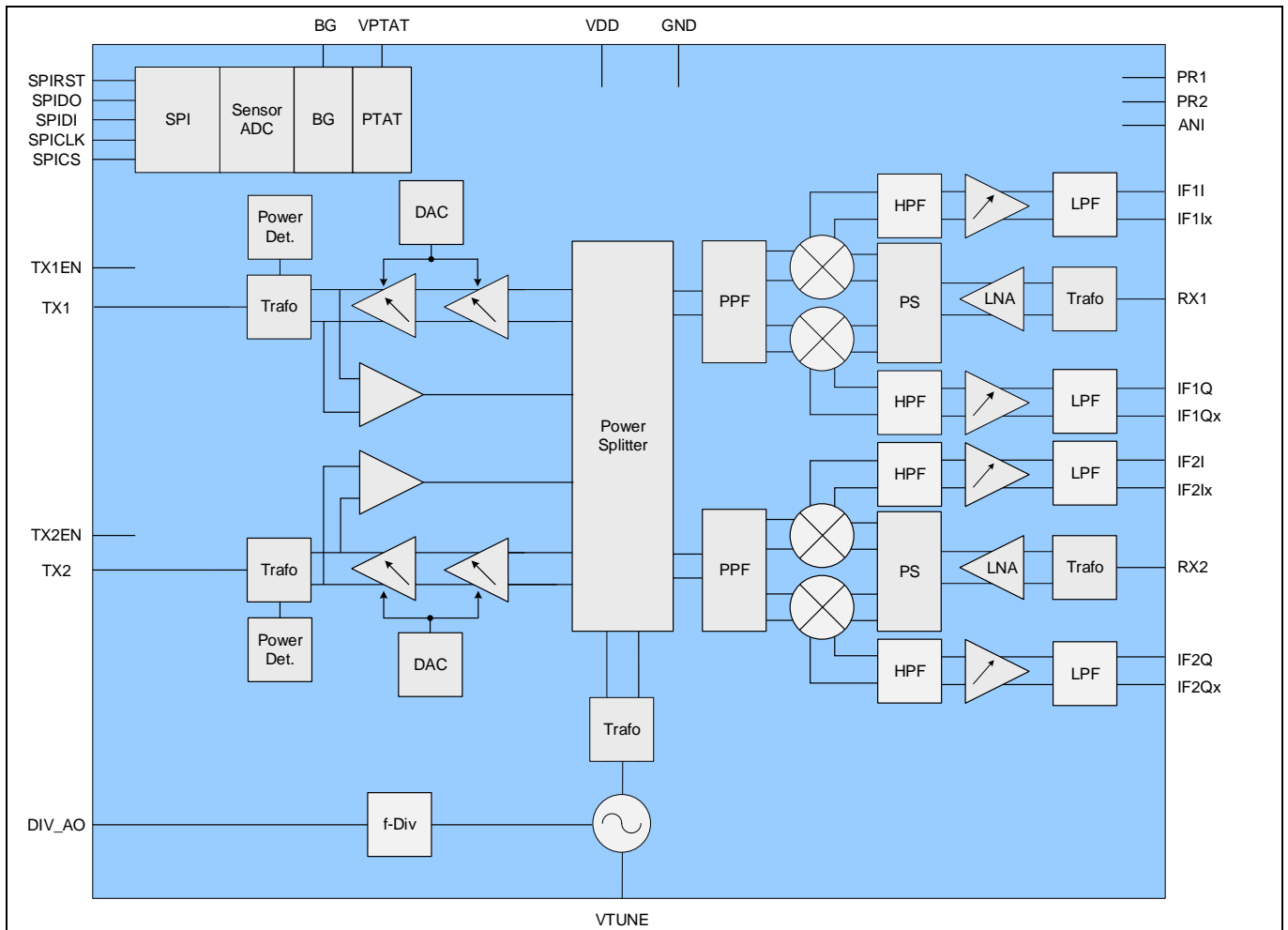
Figure 1 SPI timing diagram

Table 7 SPI Interface timing requirements

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
SPI clock period	T	20			ns	50MHz, with <1% clock jitter
Clock high time	$t_{ch}$	9			ns	
Clock low time	$t_{cl}$	9			ns	
Setup time SPIDI	$t_{mos}$	5			ns	
Hold time SPIDI	$t_{moh}$	5			ns	
Setup time SPIDO	$t_{mis}$	5			ns	
Hold time SPIDO	$t_{mih}$	1			ns	
Delay time from the output pad logic	$t_{pad\_out\_dly}$			5	ns	

### 3 Block Diagram and Pin Description

#### 3.1 Block Diagram



**Figure 2 BGT24LTR22 block diagram**



### 3.2 Pin Out

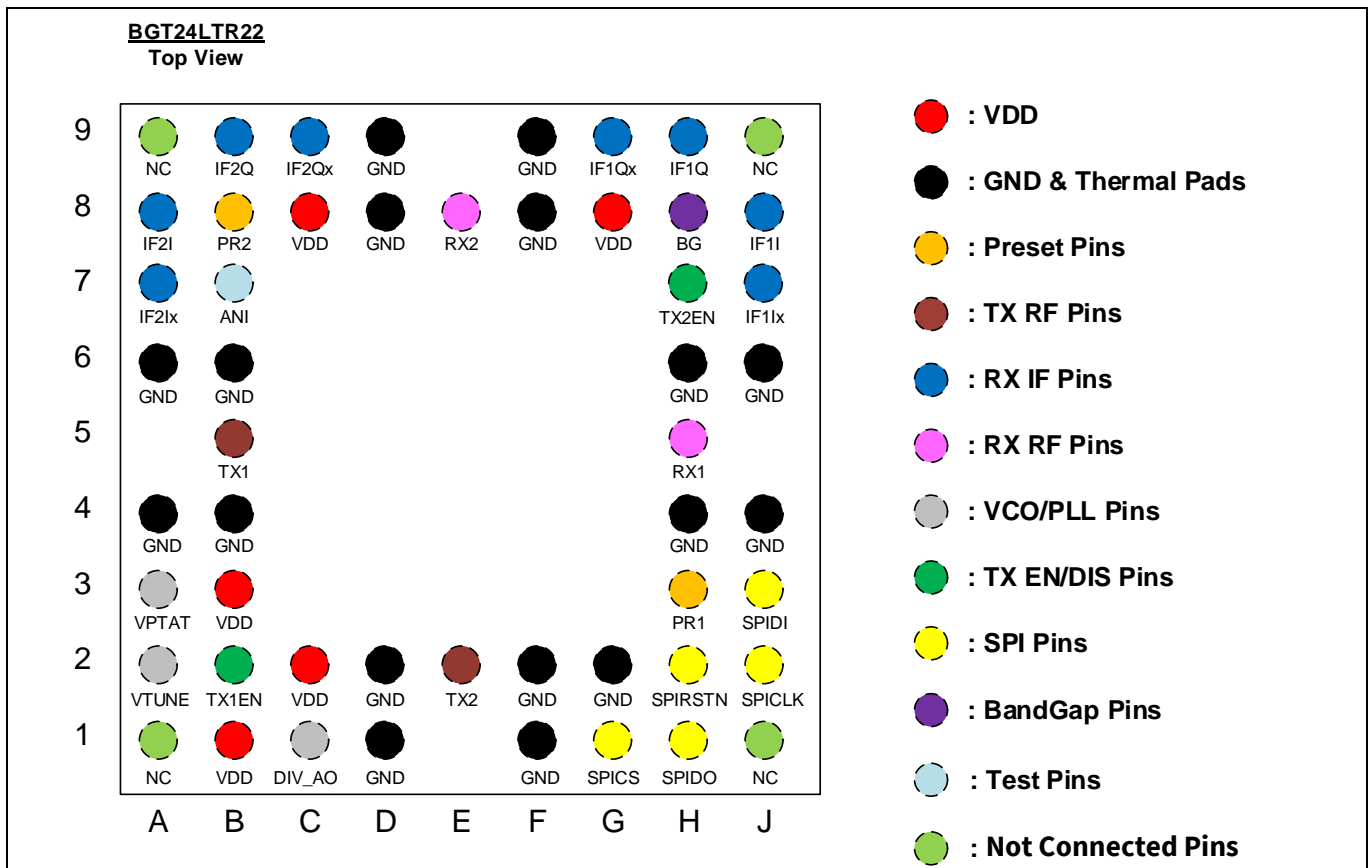


Figure 3 Pin out (top view)

### 3.3 Pin Definition and Function

Table 8 Pin definition and function

Pin Number	Name	Function
A1, A9, J1, J9	NC	No connection
B1, B3, C2, C8, G8	VDD	DC supply voltage
H5	RX1	RF input - receiver 1
E8	RX2	RF input - receiver 2
E2	TX2	Bidirectional RF I/O RF output – transmitter 2/LO input 2
B5	TX1	Bidirectional RF I/O RF output – transmitter 1/LO input 1
J8, J7	IF1I, IF1Ix	Complementary in phase downconverter IF output – receiver 1
H9, G9	IF1Q, IF1Qx	Complementary quadrature phase downconverter IF output - receiver 1
A8, A7	IF2I, IF2Ix	Complementary in-phase downconverter IF output – receiver 2

Table 8 Pin definition and function

Pin Number	Name	Function
B9, C9	IF2Q, IF2Qx	Complementary quadrature phase downconverter IF output - receiver 2
A4, A6, B4, B6, D1, D2, D8, D9, F1, F2, F8, F9, G2*, H4, H6, J4, J6	GND	Ground
H3	PR1	Mode select - pin 1
B8	PR2	Mode select - pin 2
C1	DIV_AO	Frequency divider output
B2	TX1EN	Enable transmitter 1
H7	TX2EN	Enable transmitter 2
H8	BG	Bandgap voltage output
A2	VTUNE	VCO frequency tuning input
A3	VPTAT	PTAT voltage source output
G1	SPICS	SPI chip select (spi_cs_i)
H1	SPIDO	SPI data out (spi_do_o)
H2	SPIRST	SPI reset
J2	SPICLK	SPI clock (spi_clk_i)
J3	SPIDI	SPI data in (spi_di_i)
B7	ANI	Analog input for testing

Note: *It is mandatory to connect Pin G2 to ground for SPI programming*

## 4 Package Dimensions and Footprint

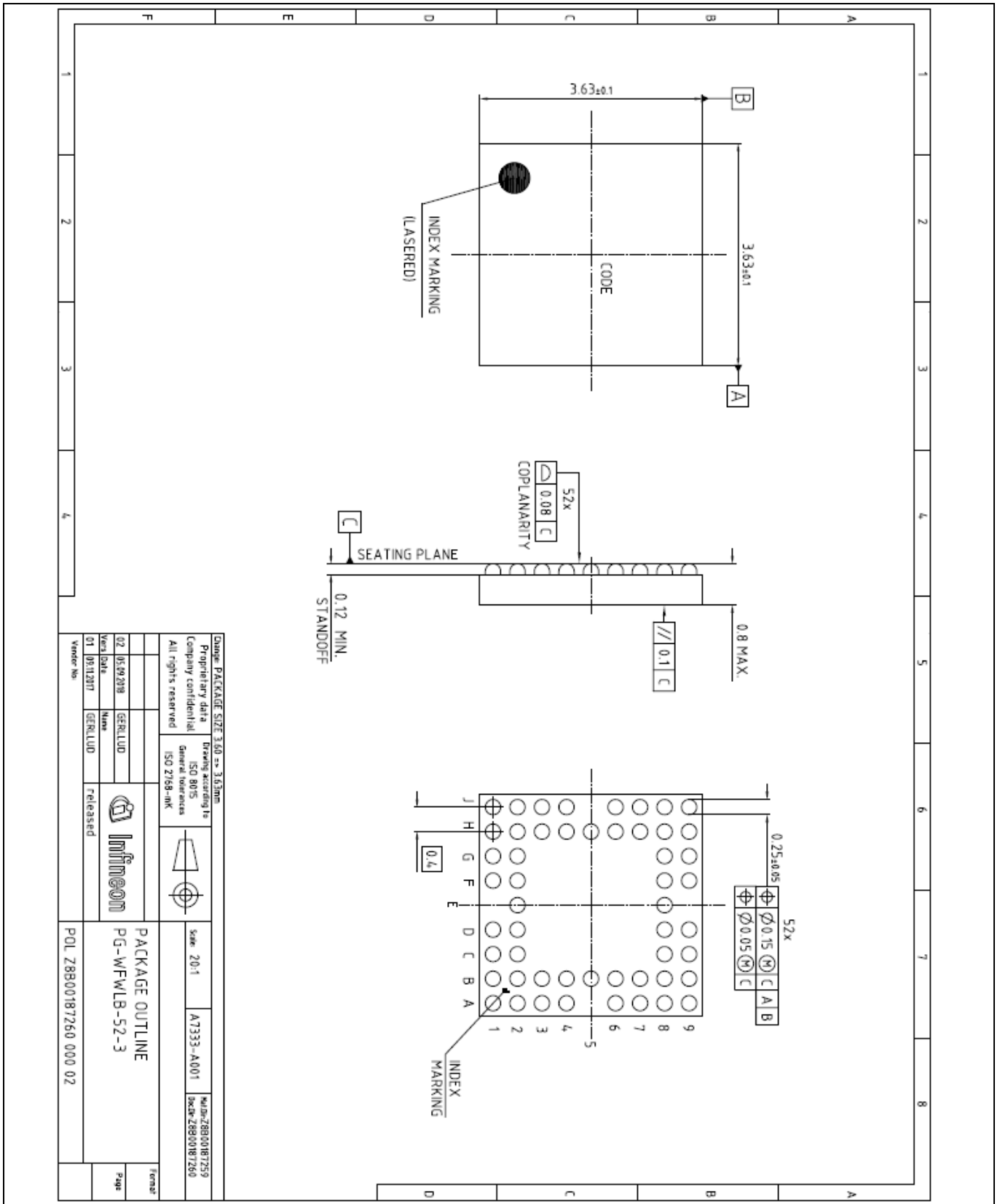
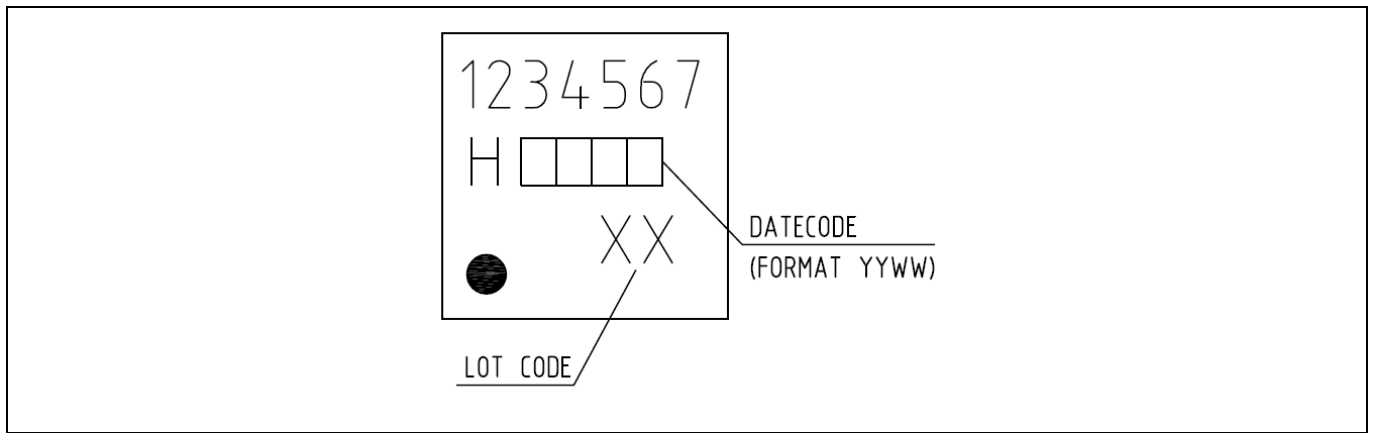


Figure 4 Package outline. Top, side and bottom view of WFWLB-52-3



**Figure 5** Marking layout of WFWLB-52-3

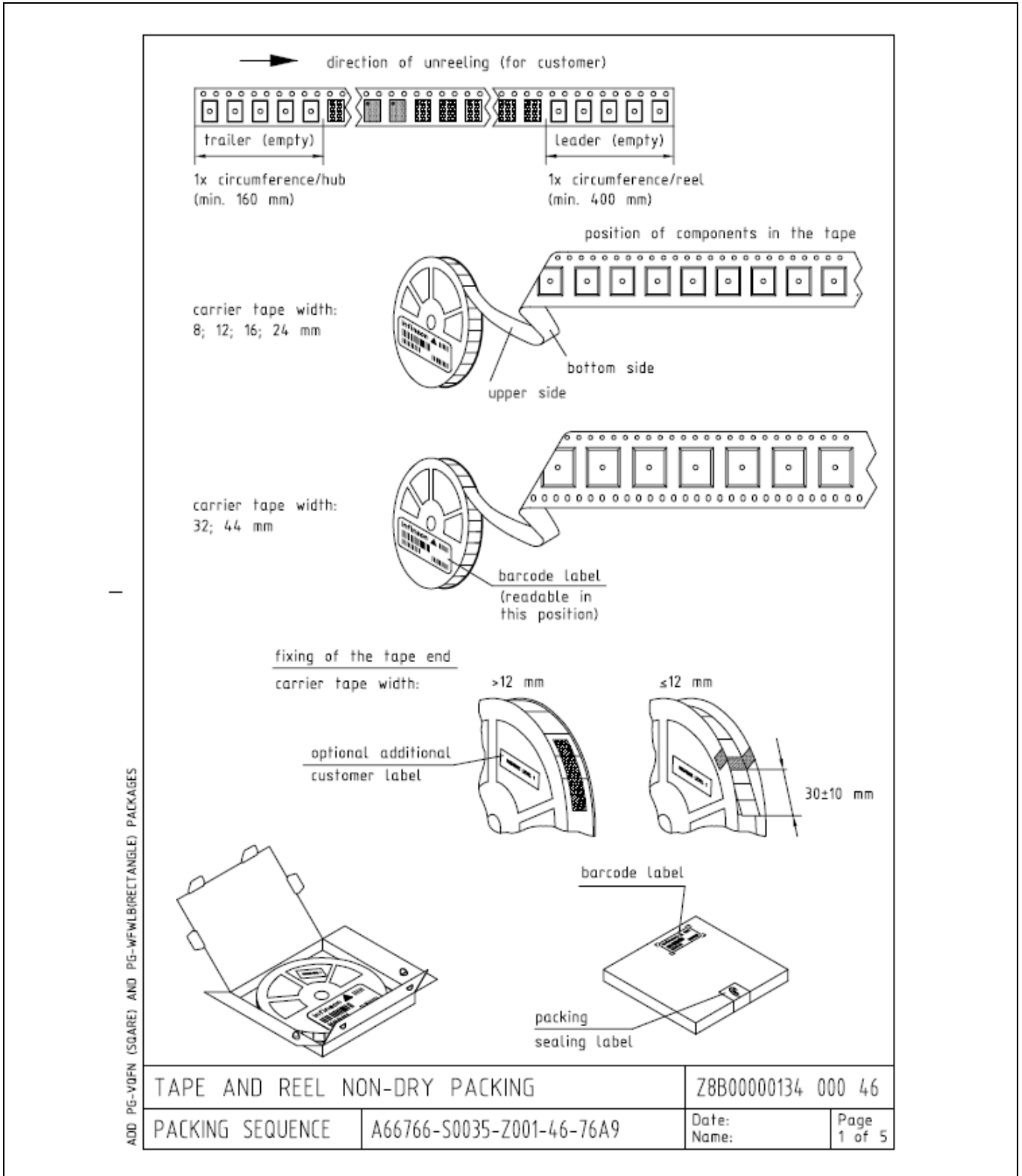


Figure 6 Tape and reel of WFWLB-52-3



Revision history

<b>Document version</b>	<b>Date of release</b>	<b>Description of changes</b>
V1.0	dd/mm/2020	First release

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